CNA1312K

Photo Interrupter

For contactless SW and object detection

Overview

CNA1312K is an ultraminiature, highly reliable transmissive photosensor in which a high efficiency GaAs infrared light emitting diode chip and a high sensitivity Si phototransistor chip are integrated in a double molded resin package.

■ Features

- Ultraminiature: 2.6 mm × 4.9 mm (height: 3.3 mm)
- Highly precise position detection: 0.1 mm
- Gap width: 2.0 mm

■ Absolute Maximum Ratings $T_a = 25$ °C

F	Symbol	Rating	Unit		
	Power dissipation *1	P_{D}	75	mW	
Input (Light emitting diode)	Forward current	I_{F}	50	mA	
	Reverse voltage	V _R	6	V.O	
Output (Photo transistor)	Collector-emitter voltage (Base open)	V _{CEO}	35	O ¹ V	
	Emitter-collector voltage (Base open)	V _{ECO}	6	V	
	Collector current	I_{C}	20	mA	
	Collector power dissipation *2	P _C	75	mW	
Operating ambient temp	Topr	-25 to +85	°C		
Storage temperature	T _{stg}	-40 to +100	°C ©		

Note) *1: Input power derating ratio is 1.0 mW/°C at $T_a \ge 25$ °C

■ Electrical-Optical Characteristics $T_a = 25$ °C±3°C

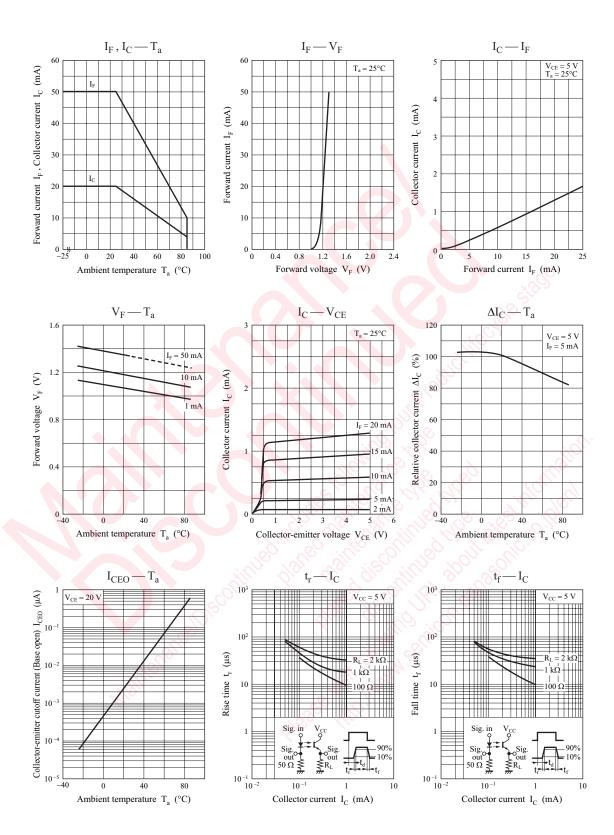
Parameter		Symbol	Conditions	Min	Тур	Max	Unit
Input characteristics	Reverse current	I_R	$V_R = 3 V$			10	μА
	Forward voltage	V _F	$I_F = 20 \text{ mA}$		1.2	1.4	V
Output characteristics	Collector-emitter cutoff current (Base open)	I _{CEO}	$V_{CE} = 20 \text{ V}$			100	nA
Transfer characteristics	Collector current	$I_{\rm C}$	$V_{CE} = 5 \text{ V}, I_F = 5 \text{ mA}$	40		400	μΑ
	Collector-emitter saturation voltage	V _{CE(sat)}	$I_F = 10 \text{ mA}, I_C = 50 \mu\text{A}$			0.4	V
	Rise time *	t _r	$V_{CC} = 5 \text{ V}, I_{C} = 0.1 \text{ mA},$		50		μs
	Fall time *	t_{f}	$R_{\rm L} = 1000\Omega$		50		μs

Note) 1. Input and output are practiced by electricity.

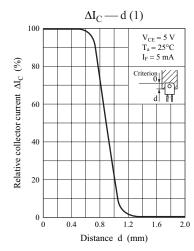
2. This device is designed by disregarding radiation.

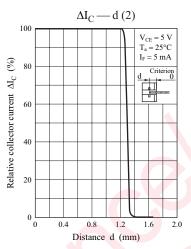
3. *: Switching time measurement circuit V_{CC} (Input pulse) V_{CC} (Output pulse) V_{CC} V_{CC} (Output pulse) V_{CC} V_{CC}

^{*2:} Output power derating ratio is 1.0 mW/°C at $T_a \ge 25$ °C



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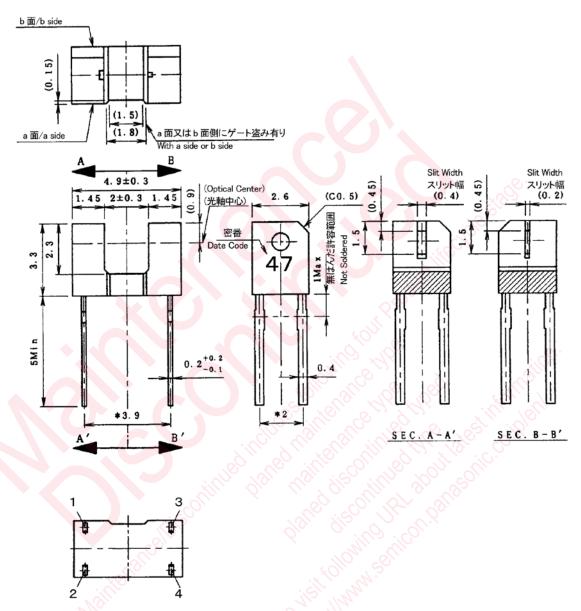




CNA1312K Panasonic

■ Package (Unit: mm)

LSMSIN4S0003



- (注 1) *リード根元寸法とします。/(Note1)*Indicates root dimensions of lead.
- (注 2) 指示無き寸法公差は±0.2。/(Note2)Not appointment tolerance :±0.2.
- (注3) 密番は、目視又は顕微鏡に於いて解読できる事。

(Note3)What a date code sees an attention and can decode in a microscope.

- Pin name
 - 1: Anode
 - 2: Cathode
 - 3: Collector
 - 4: Emitter

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